

SANYO

No.4668

2SA1723

PNP Epitaxial Planar Silicon Transistor
 High-Frequency Amp, Medium-Power
 Amp Applications

Applications

- Wideband amplifiers.
- High-frequency drivers.

Features

- High f_T ($f_T = 1.5\text{GHz typ}$).
- High current ($I_C = 300\text{mA}$).
- Adoption of FBET process.

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	-30	V
Collector-to-Emitter Voltage	V_{CEO}	-20	V
Emitter-to-Base Voltage	V_{EBO}	-3	V
Collector Current	I_C	-300	mA
Collector Current(Pulse)	I_{CP}	-600	mA
Collector Dissipation	P_C	1.2	W
		5	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

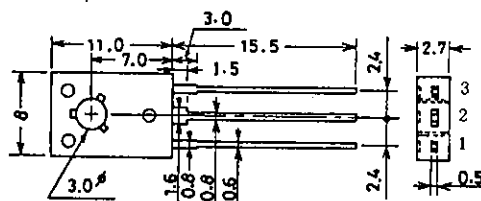
$T_c = 25^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = -2\text{V}, I_C = 0$			-1.0	μA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -50\text{mA}$	15		100	
	$h_{FE(2)}$	$V_{CE} = -5\text{V}, I_C = -300\text{mA}$	5			
Gain-Bandwidth Product	f_T	$V_{CE} = -5\text{V}, I_C = -100\text{mA}$		1.5		GHz
Output Capacitance	C_{ob}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		5.8		pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = -10\text{V}, f = 1\text{MHz}$		5.0		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$	-0.4		-1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -10\text{mA}$	-0.9		-1.2	V

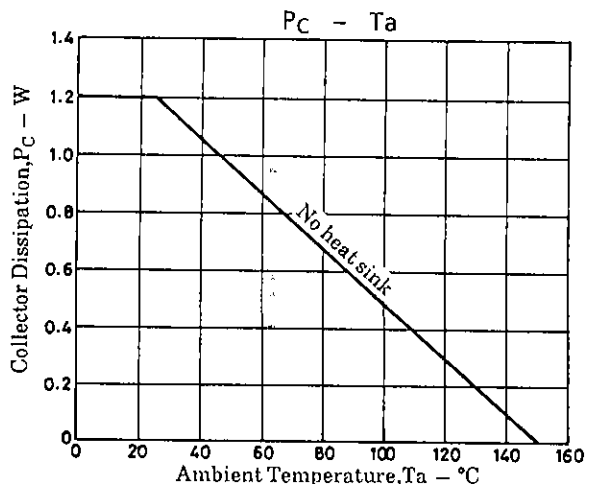
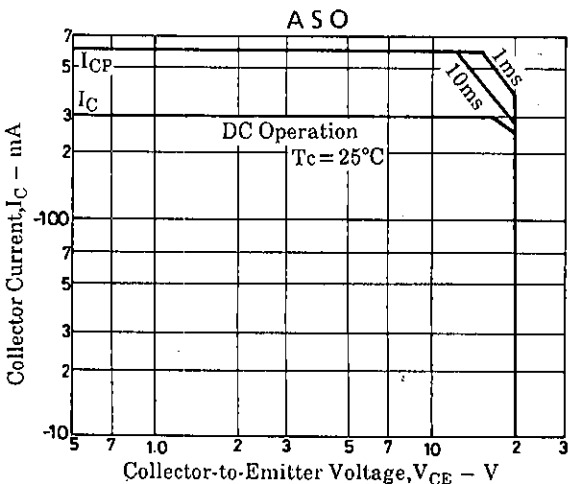
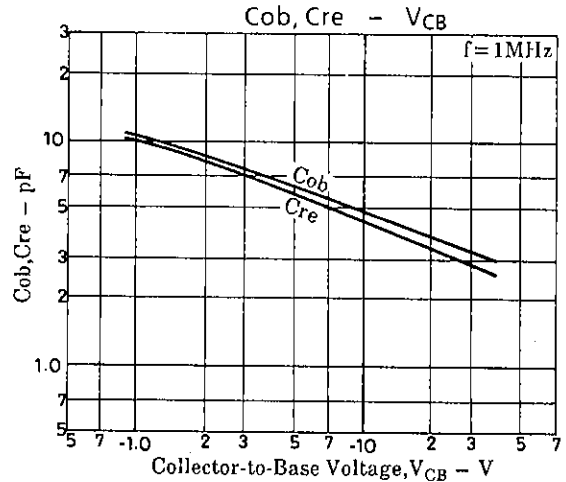
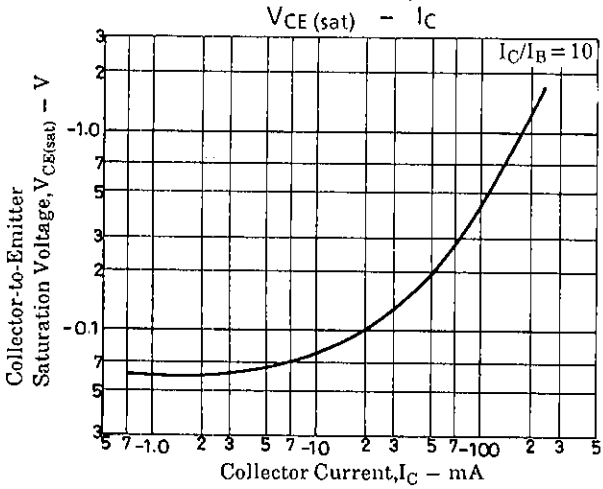
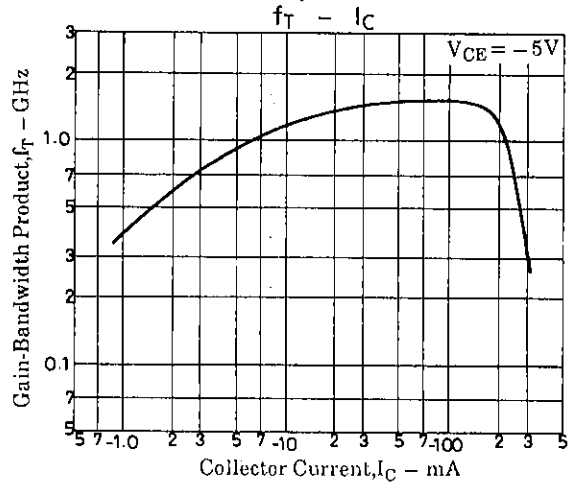
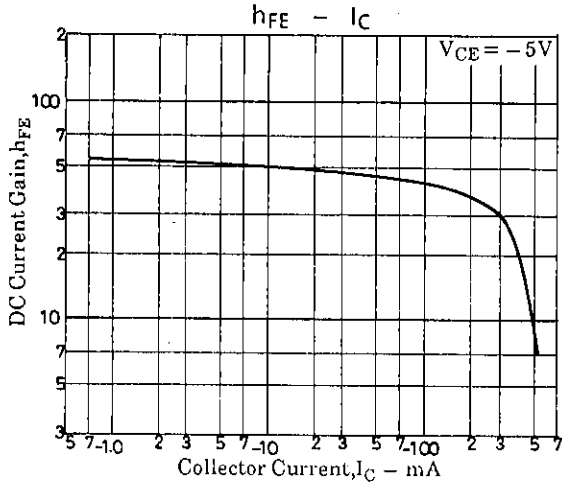
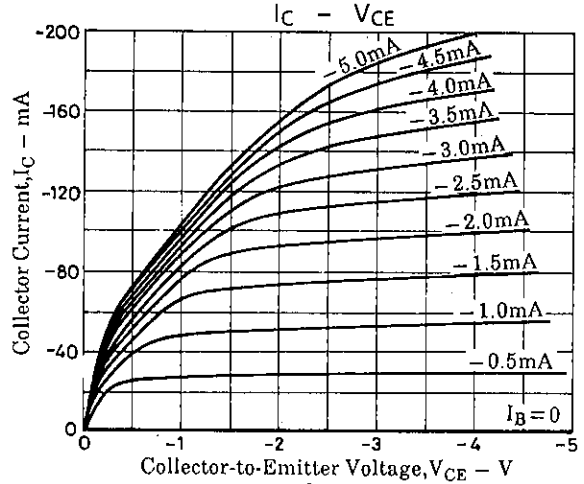
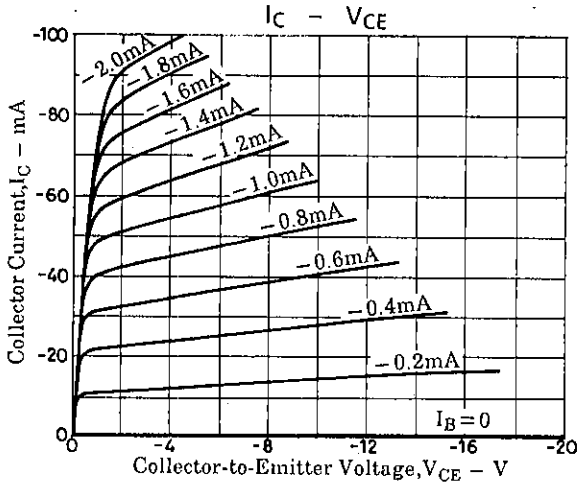
Package Dimensions 2009B

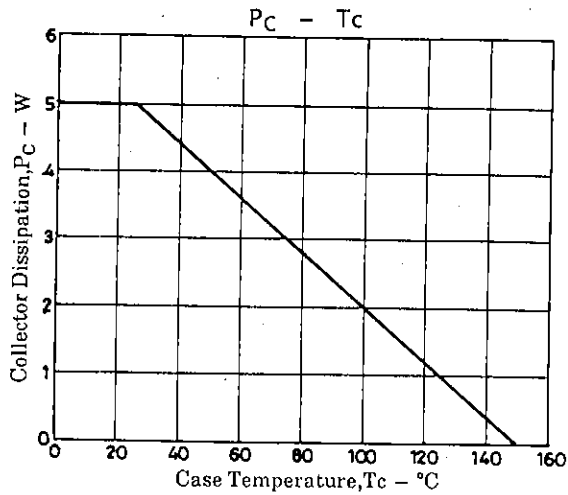
(unit: mm)



JEDEC: TO-126

1: Emitter
 2: Collector
 3: Base





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